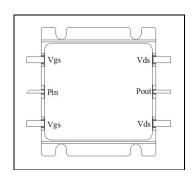


## 0.8-2.5GHz, 80W, GaN Fully matched PA Module

## **Description**

The GMAH0825-80H3 is a 80-watt, single stage integrated Power Amplifier Module, designed for broad band applications, with frequencies from 0.8 to 2.5GHz. The module is 50  $\Omega$  input/output matched and requires minimal external components. It can work at higher voltage up to 36V with increased power capability

The module implements multiple GaN active dice and its matching network within highly compact 30.8\*27.4mm metal RF package with excellent capability for heat dissipation.



| ,     | VDS=32V | IDQ:  | =150mA | VGS  | =-2.75V | CW   | Harmonics ( | Pout=Psat) |
|-------|---------|-------|--------|------|---------|------|-------------|------------|
| F     | Pin     | Psat  | Psat   | I    | Gain    | Eff  | 2nd         | 3rd        |
| (MHz) | (dBm)   | (dBm) | (W)    | (A)  | (dB)    | (%)  | (dBc)       | (dBc)      |
| 700   | 38.18   | 48.79 | 75.7   | 3.45 | 10.61   | 68.6 | 11.00       | 13.50      |
| 800   | 36.9    | 49.51 | 89.3   | 4.13 | 12.61   | 67.6 | 13.6        | 14.7       |
| 900   | 37.27   | 49.94 | 98.6   | 4.72 | 12.67   | 65.3 | 20.7        | 13.9       |
| 1000  | 36.2    | 50.12 | 102.8  | 5.06 | 13.92   | 63.5 | 25.0        | 15.5       |
| 1100  | 37.36   | 50.4  | 109.6  | 5.71 | 13.04   | 60.0 | 17.8        | 16.8       |
| 1200  | 37.35   | 50.55 | 113.5  | 6.06 | 13.2    | 58.5 | 26.0        | 18.0       |
| 1300  | 39      | 51.29 | 134.6  | 6.94 | 12.29   | 60.6 | 23.3        | 16.7       |
| 1400  | 38      | 50.93 | 123.9  | 6.6  | 12.93   | 58.7 | 23.8        | 19.4       |
| 1500  | 38.83   | 51.13 | 129.7  | 6.78 | 12.3    | 59.8 | 30.6        | 23.3       |
| 1600  | 38.94   | 51.07 | 127.9  | 7    | 12.13   | 57.1 | 30.5        | 27.8       |
| 1700  | 38.5    | 51.01 | 126.2  | 7.16 | 12.51   | 55.1 | 24.5        | 26.2       |
| 1800  | 39      | 51.13 | 129.7  | 7.29 | 12.13   | 55.6 | 24.4        | 24.4       |
| 1900  | 39.05   | 51.1  | 128.8  | 7.24 | 12.05   | 55.6 | 19.8        | 17.9       |
| 2000  | 39.11   | 50.75 | 118.9  | 6.56 | 11.64   | 56.6 | 19          | 12.8       |
| 2100  | 38.6    | 50.65 | 116.1  | 6.47 | 12.05   | 56.1 | 31.5        | 16.4       |
| 2200  | 38.93   | 50.63 | 115.6  | 6.81 | 11.7    | 53.1 | 29.2        | 18.2       |
| 2300  | 39.4    | 50.53 | 113.0  | 6.42 | 11.13   | 55.0 | 30.8        | 17.3       |
| 2400  | 38.5    | 50.25 | 105.9  | 6.09 | 11.75   | 54.4 | 36          | 15.9       |
| 2500  | 38.61   | 49.74 | 94.2   | 5.56 | 11.13   | 52.9 | 42          | 24.5       |

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### **Product Features**

- Operating Frequency Range: 0.8-2.5GHz
- Operating Drain Voltage(Recommended): +32 V (up to 36V with power increased >100W)
- 50 Ω Input/Output (External DC block capacitor needed)
- Psat≥49 dBm (CW)
- Small signal gain:>13dB, Power gain:>11dB
- Minimum efficiency:>50%
- 30.8\*27.4 mm metal RF package
- Compliant to Restriction of Hazardous Substances (RoHS) Directive 2002/95/EC

## **Applications**

- Ultra Broadband Amplifiers, typically 0.8-2.5GHz, 1-2GHz,0.8-2.2GHz
- L band power amplifier, typically 960-1215MHz, 1200-1400MHz.1400-1600MHz
- Test Instrumentation
- EMC Amplifier Drivers
- 2-way Radios

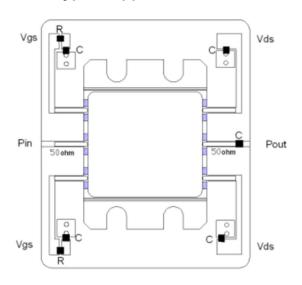
#### **Table 1. Maximum Ratings**

| Rating                         | Symbol           | Value       | Unit |
|--------------------------------|------------------|-------------|------|
| DrainSource Voltage            | V <sub>DSS</sub> | 150         | Vdc  |
| GateSource Voltage             | V <sub>GS</sub>  | -10 to +2   | Vdc  |
| Operating Voltage              | V <sub>DD</sub>  | +36         | Vdc  |
| Storage Temperature Range      | Tstg             | -65 to +150 | °C   |
| Case Operating Temperature     | T <sub>c</sub>   | +150        | °C   |
| Operating Junction Temperature | T₃               | +225        | °C   |

### **Table 2. Thermal Characteristics**

| Characteristic                       | Symbol | Value | Unit |
|--------------------------------------|--------|-------|------|
| Thermal Resistance, Junction to Case | Rejc   | 1.2   | °C/W |
| T <sub>C</sub> = 25°C, Pout=90W, FEA |        | 1.5   |      |

## Typical application circuit





## TYPICAL CHARACTERISTICS

Figure 1. Network analyzer output S11/S21 (Pin=0dBm)

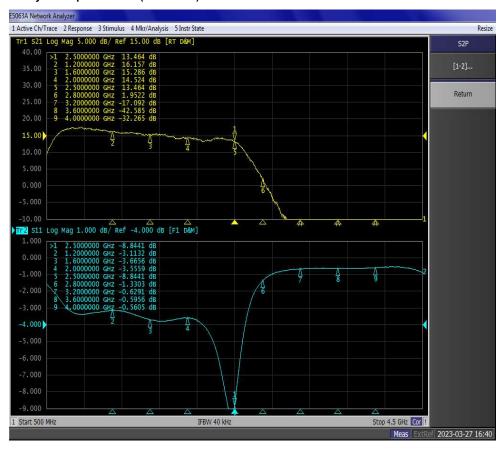
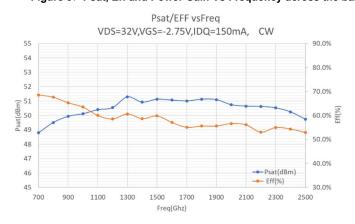
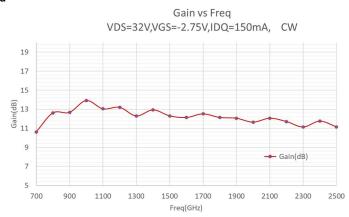


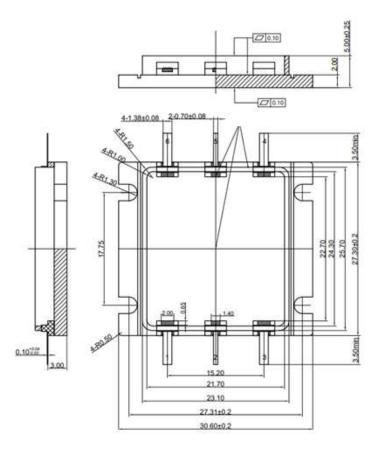
Figure 3. Psat, Eff and Power Gain Vs Frequency across the band





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## Package Dimensions (Unit:mm)



#### **Revision history**

Table 6. Document revision history

| Date      | Revision | Datasheet Status      |
|-----------|----------|-----------------------|
| 2023/3/29 | Rev 1.0  | Preliminary Datasheet |
|           |          |                       |
|           |          |                       |

#### Application data based on SYX-23-10

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